N-Channel Enhancement Mode Power MOSFET

Description

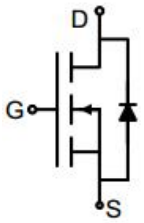
The GT048N10T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} 100V
- I_D (at V_{GS} = 10V) 110A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 4.8mΩ
- $R_{DS(ON)}$ (at V_{GS} = 4.5V) < 6.5mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-220

Ordering Information

Device	Package	Marking	Packaging
GT048N10T	TO-220	GT048N10	50pcs/Tube

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Continuous Drain Current	T_C = 25ºC	I_D	110	A
	T_C = 100ºC		70	
Pulsed Drain Current (note1)		I_{DM}	440	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	150	W
Single pulse avalanche energy （note2）		E_{AS}	210	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	ºC/W
Thermal Resistance, Junction-to-Case	R_{thJC}	0.83	ºC/W

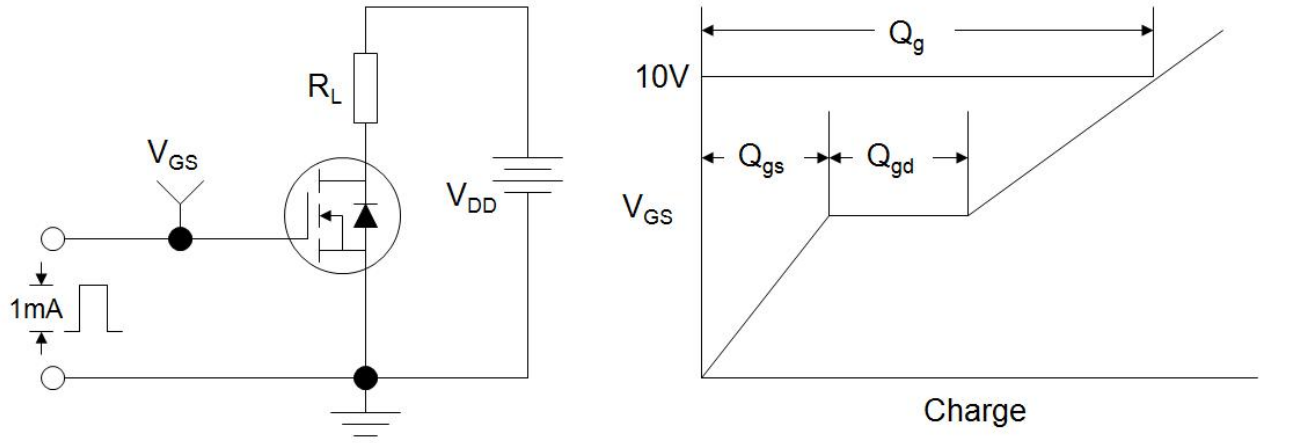
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 20A	--	4.4	4.8	mΩ
		V_{GS} = 4.5V, I_D = 20A	--	5.2	6.5	
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 20A	--	49	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 0.8MHz	--	3220	--	pF
Output Capacitance	C_{oss}		--	1225	--	
Reverse Transfer Capacitance	C_{rss}		--	9	--	
Total Gate Charge	Q_g	V_{DD} = 50V, I_D = 20A, V_{GS} = 10V	--	68	--	nC
Gate-Source Charge	Q_{gs}		--	8	--	
Gate-Drain Charge	Q_{gd}		--	16	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 50V, I_D = 20A, R_G = 2.2Ω	--	13	--	ns
Turn-on Rise Time	t_r		--	27	--	
Turn-off Delay Time	$t_{d(off)}$		--	24	--	
Turn-off Fall Time	t_f		--	5	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	110	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 20A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 20A, V_{GS} = 0V di/dt=600A/us	--	116	--	nC
Reverse Recovery Time	Trr		--	25	--	ns

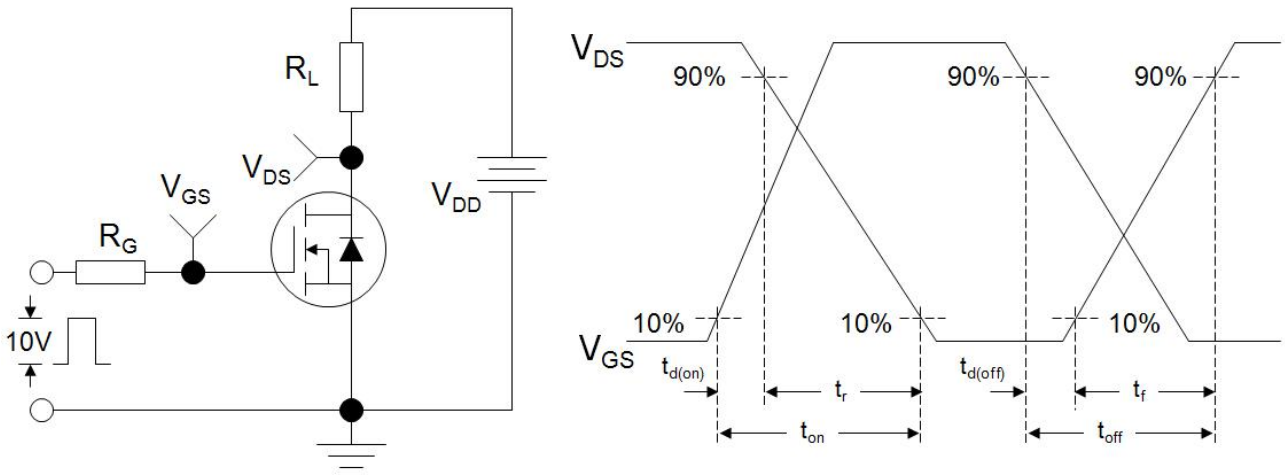
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 570mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

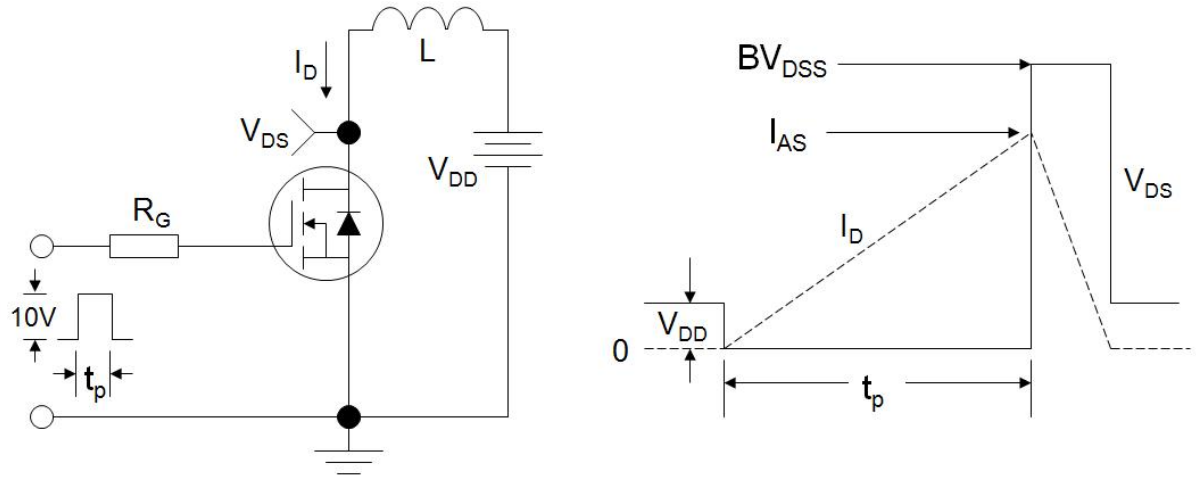
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

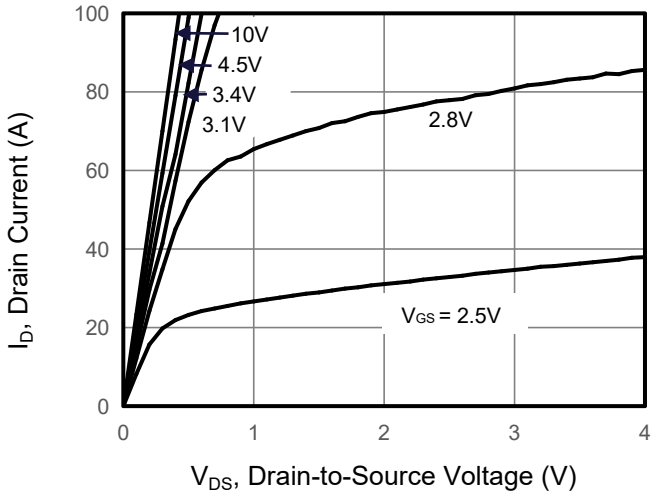


Figure 2. Transfer Characteristics

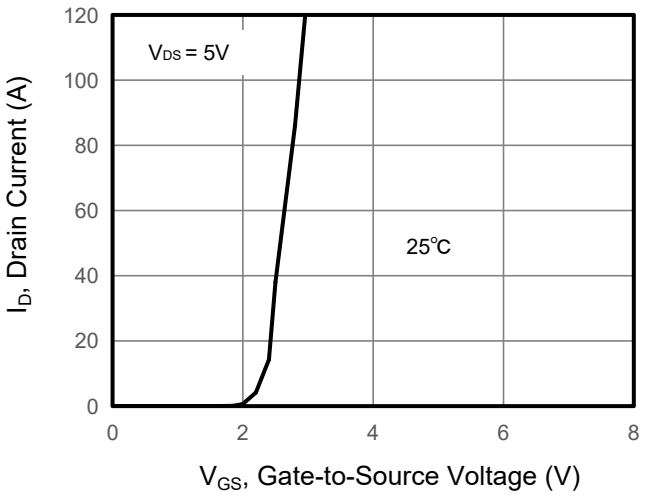


Figure 3. Drain Source On Resistance

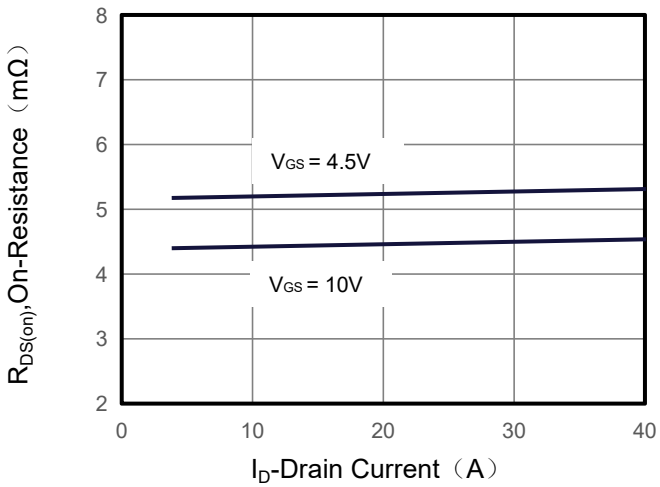


Figure 4. Gate Charge

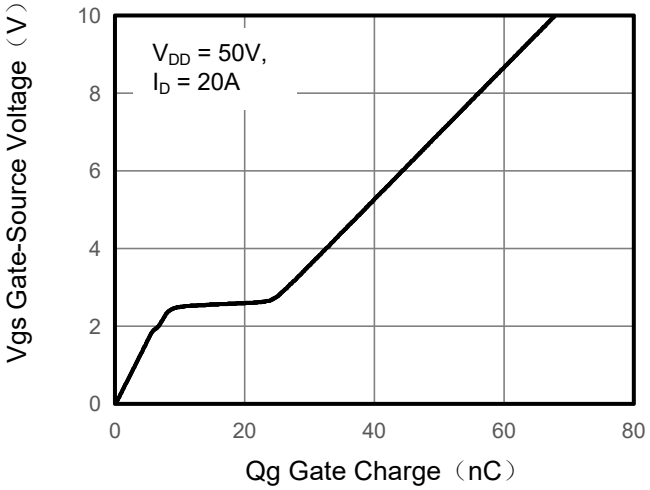


Figure 5. Capacitance

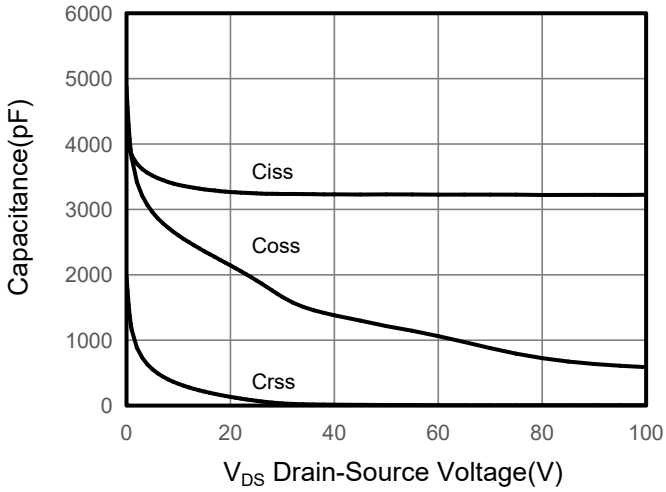
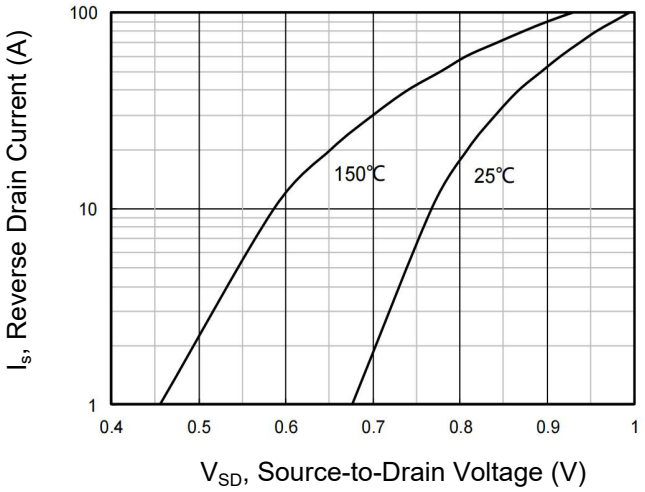


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

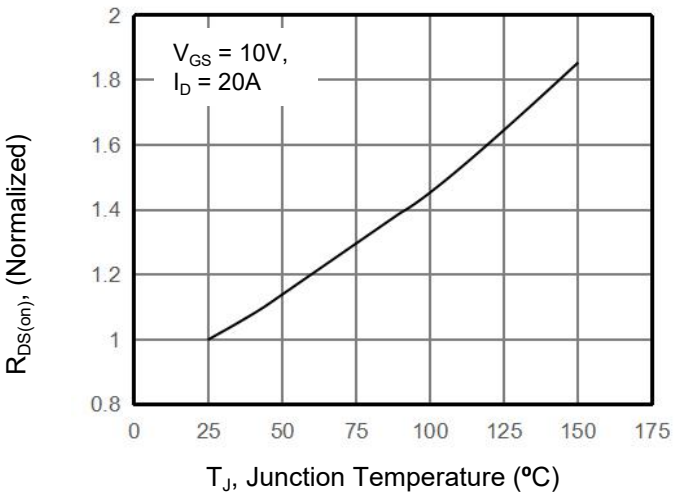


Figure 8. Safe Operation Area

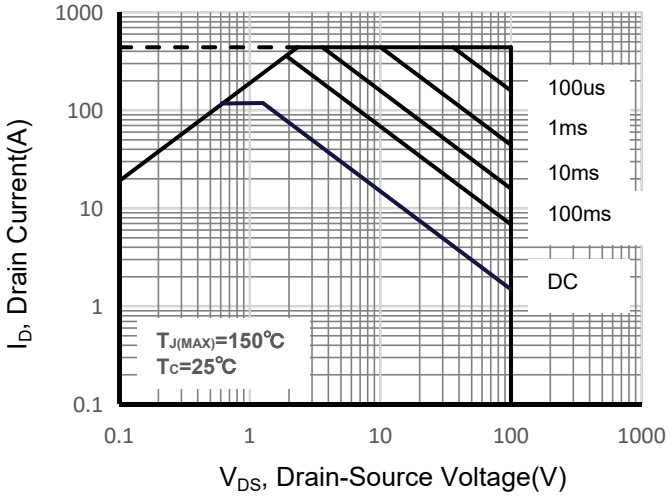


Figure 9. Maximum Continuous Drain Current vs Case Temperature

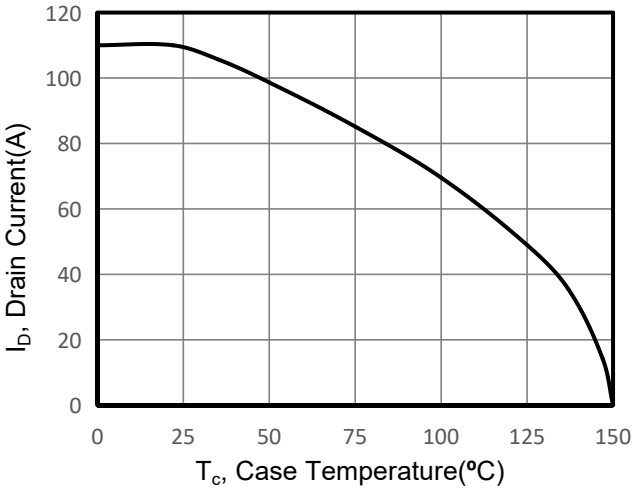
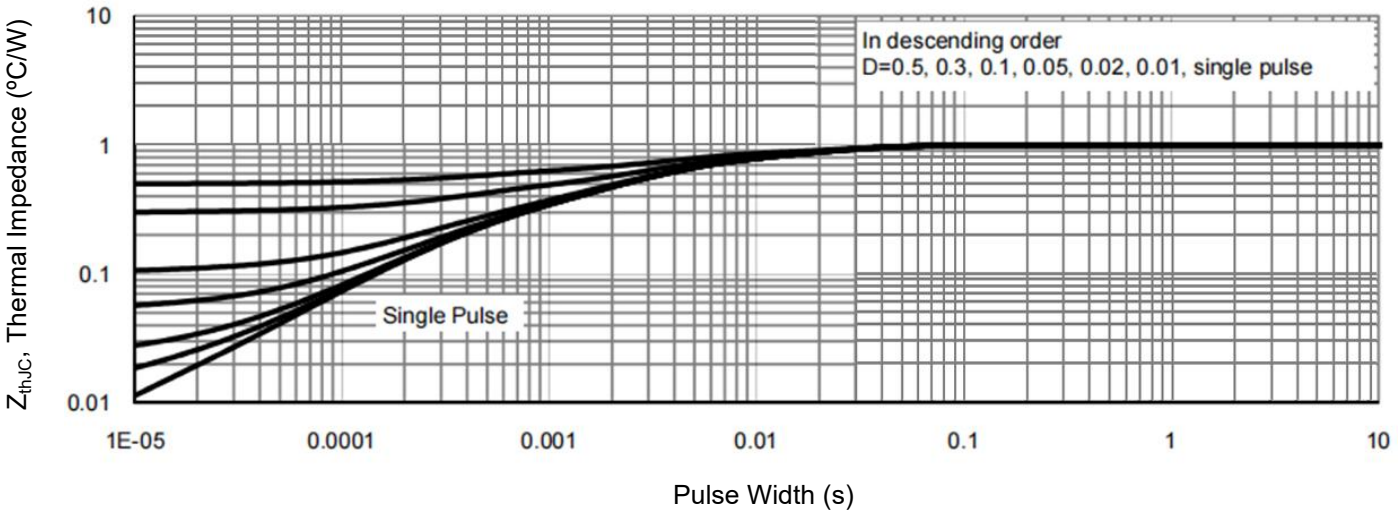
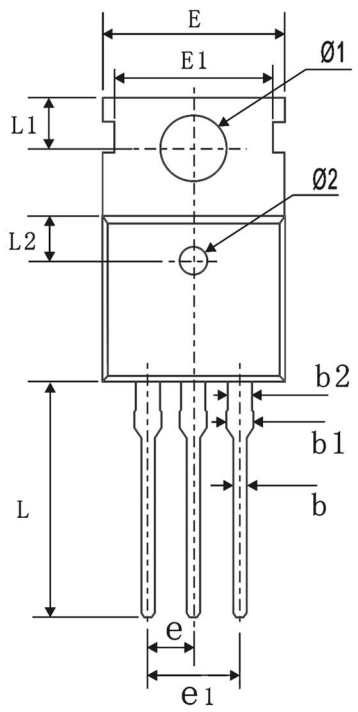


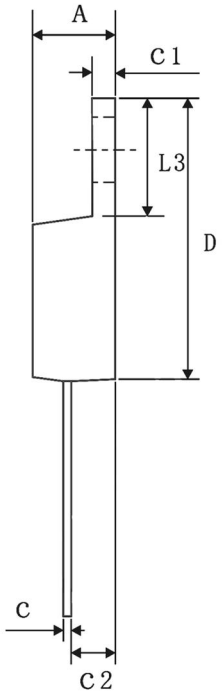
Figure 10. Normalized Maximum Transient Thermal Impedance



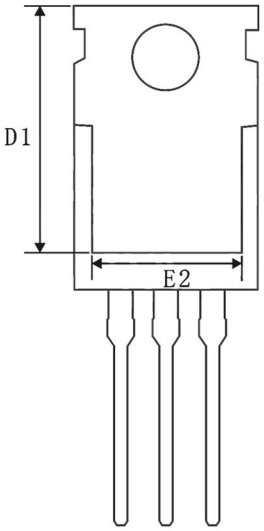
TO-220 Package Information



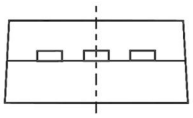
TOP VIEW



SIDE VIEW



BOTTOM VIEW



SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
b	0.70	0.80	0.90
b1	——	——	1.42
b2	1.17	1.27	1.37
c	0.40	0.50	0.60
c1	1.25	1.30	1.35
c2	2.20	2.40	2.60
D	15.45	15.65	15.85
D1	13.20	13.40	13.60
E	9.80	10.0	10.2
E1	8.60	8.70	8.80
E2	7.80	8.00	8.20
e1	4.88	5.08	5.28
L	12.95	13.15	13.35
L1	2.70	2.80	2.90
L2	2.40	2.50	2.60
L3	6.30	6.50	6.70
Ø1	3.50	3.60	3.70
Ø2	1.35	1.50	1.65
e	2.54BSC		